

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

1. (Canceled)
2. (Canceled)
3. (Canceled)
4. (Currently amended) An etching solution according to Claim 17 ~~+~~, wherein said ~~comprising a~~ solvent mixture ~~consisting~~ consists essentially of ethylene glycol and glycerol in a mixing ratio of from 1:10 to 10:1.
5. (Currently amended) An etching solution according to Claim 17 ~~+~~, wherein said ~~comprising a~~ solvent mixture ~~consisting~~ consists essentially of ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.
6. (Canceled)
7. (Currently amended) An etching solution according to Claim 17 ~~+~~, wherein the individual components are of high-purity ~~comprising a mixture of high-purity individual components.~~
8. (Withdrawn) A method for the selective etching of doped silicate layers comprising treating said doped silicate layers with an etching solution according to Claim 17.
9. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron doped glass.
10. (Withdrawn) A method according to claim 8, wherein said doped silicate is phosphorous doped glass.

11. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron-phosphorous doped glass.
12. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a spin etcher.
13. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a drip etcher.
14. (Currently amended) An etching solution according to Claim 17 +, wherein the amount of said water is 6.4 -20 % by weight.
15. (Canceled)
16. (Canceled)
17. (Previously presented) An etching solution for the production of integrated circuits consisting essentially of  
5- 20% by weight hydrofluoric acid,  
a solvent mixture consisting essentially of at least two of ethylene glycol, propylene glycol, ethanol, and glycerol,  
and  
1-20 % by weight water.
18. (Previously presented) An etching solution according to claim 17, wherein the amount of hydrofluoric acid is 10- 20% by weight .
19. (Previously presented) An etching solution according to claim 17, wherein the amount of hydrofluoric acid is 15- 20% by weight .